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(71) Applicant *(for all designated States except US)*: TEIJIN LIMITED [JP/JP]; 6–7, Minamihommachi 1–chome, Chuo–ku, Osaka–shi, Osaka 541–0054 (JP).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: TOMIE, Takashi [JP/JP]; Teijin Limited, Tokyo Research Center, 3–2, Asahigaoka 4–chome, Hino–shi, Tokyo 191–0065 (JP). EBINA, Atsushi [JP/JP]; Teijin Limited, Mihara Factory, 1–1, Enichi–cho 1–chome, Mihara–shi, Hiroshima 723–0015 (JP). IKEDA, Yoshinori [JP/JP]; Teijin Limited, Mihara Factory, 1–1, Enichi–cho 1–chome, Mihara–shi, Hiroshima 723–0015 (JP).

(74) Agents: ISHIDA, Takashi et al.; A. Aoki, Ishida & Associates, Toranomon 37 Mori Building, 5–1, Toranomon 3–chome, Minato–ku, Tokyo 105–8423 (JP).

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(54) Title: PHASE CHANGE–TYPE OPTICAL RECORDING MEDIUM AND PROCESS FOR MANUFACTURING THE SAME

(57) Abstract

A phase change–type optical recording medium in which recording of information is made utilizing phase change by light, comprising: a substrate; a first dielectric layer on said substrate; a phase change–type optical recording layer made of GeSbTe wherein the molar ratio of Sb:Te is less than 0.6 on said first dielectric layer; a second dielectric layer on said phase change–type optical recording layer; and a reflective layer either on the second dielectric layer or between said substrate and said first dielectric layer; wherein an intermediate layer is further disposed between said first dielectric layer and said phase change–type optical recording layer and/or between said phase change–type optical recording layer and said second dielectric layer, said intermediate layer being a single layer of Sb_2Te_3 or GeTe or a laminate layer of Sb2Te3 and GeTe, said intermediate layer being in direct contact with said phase change–type optical recording layer.